FINAL SOLUTION

EECC140 Coming 2015 Final	3	/12
EECS140 Spring 2015 Final	4+5	/16
Name Mr B+ student.	6	/10
	7+8	/24
SID	9	/20
	10+11	/22
	12+13	/22
1) [10] You need an amplifier with a gain of 10 at 10Mrad/s, and the	14	/16
gain must be accurate to 0.1%. You decide to use an op-amp in		710
feedback. You may assume that the ratio of passives is perfect.	Total	/160
a) What is the minimum low frequency gain of your op-amp?		
f=0el Af < 103 A> 104=104		
b) What is the minimum unity gain frequency of your op-amp?		
Wa > A Wp = 104107 = 10" rester		
c) If your amplifier must drive a 1pF load capacitor, what is the mi	inimum g _m	
required in the differential pair? $ \omega_{\alpha} = \frac{g_{\alpha}}{G_{\alpha}} g_{\alpha} > \omega_{\alpha} C_{\alpha} = 10^{11} \text{for antial pair} $		
$W_{\alpha} = \frac{1}{C_{L}}$ $g_{m} > W_{\alpha} C_{L} = 10 / 0 = 0.15$	ir?	
	- onti	
e) Explain why your answer to 1c is the same whether the op-amp	is a two-stage	e or a
single-stage. Single stope wa = gm Two stope in feedback assure PM > 450, so wa = gm		
a ci	1 34	1 9 9
Two stage in feedback assure PM > 450, so an - CZ	PZ	w, 2/2 - E,
2) [8] Assume that you are working with a single-sided supply of 5V i	in a technolog	.y
with Vtn= Vtp =1V and you can choose from the following opamp	topologies:	
(1) NMOS input folded cascode		
(2) PMOS input folded cascode(3) NMOS input 2 stage Miller compensated		
(4) PMOS input 2 stage Miller compensated		
(5) NMOS input folded cascode with output stage		
(6) PMOS input folded cascode with output stage		
Which will work for each of the following applications (write all the n	umbers that w	<i>i</i> ill
work for each)		
a) an opamp in unity-gain feedback with input from 2 to 5V and c	capacitive load	1.
b) a switched capacitor amplifier with a gain of +10 and input from	m 0 to 0.5V.	
6		to 1V
c) an amplifier with a gain of 2 driving a $1k\Omega$ resistive load and in	nput nom 0.5	
d) a unity-gain amplifier with input from 1.5 to 3.5V		
123456		

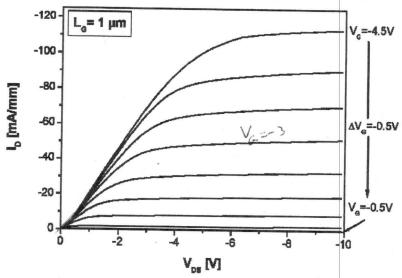
Score

/18

Prob.

1+2

3) [12] The data in the figure below is taken from a PMOS transistor made out of diamond. The source is grounded, the drain voltage varies from 0 to -10V. The gate voltage varies from -0.5 to -4.5V in steps of -0.5V. Drain current is given in mA per millimeter of Width. Assume that you have a transistor that with W/L = 1000u/1u, so the vertical axis can be read as mA.



(from Kunze, et al., Carbon 37 (1999).)

- 2 a) estimate the threshold voltage, Vtp = -0.5V
- b) estimate g_m when V_G =-3V and the device is in saturation

estimate
$$g_m$$
 when $V_G=-3V$ and the device is in saturation
$$\Delta I = 20 \text{ mA}$$

$$\Delta V = 0.5 V$$
c) estimate r_0 when $V_G=-3V$ and the device is in saturation
$$\Delta I = I \text{ mA}$$

$$R_0 = \frac{4V}{RI} = \frac{5V}{I_{N,Q}} = 5K$$
or when $V_G=-4.5V$ and $V_{DS}=0$

- e) if this device is used as a PMOS common source amplifier with an ideal current source load at a gate bias of V_G=-3V,
 - (1) sketch the circuit, including the magnitude (in mA) of the current source
 - (2) roughly what gain will it have?

(2) roughly what gain will it have?

$$A_{V} = -\frac{(40ms)(5K)}{50mA} = -206$$

- 4) [10] Your colleague creates a new transistor with a drain current given by I_d= a V_g V_d when the source is grounded. a has units of [A/V²].
 a) write a formula for g_m in terms of a, V_g, and V_d
 b) write a formula for r_o in terms of a, V_g, and V_d
 c) write a formula for the gain in terms of a, V_g, and V_d
- d) for proper operation, you have to bias the gate and drain at values between 0.1V or 1V. Which values should you choose to maximize the gain?
 - 5) [6] You are helping another colleague make measurements on an amplifier circuit in a box with three terminals labeled IN, OUT, and GND. You apply voltages from GND to IN and GND to OUT and measure the current as shown in the table below.

 a) What is G_M for the amplifier?
- b) What is R_0 for the amplifier?
 - c) If you disconnect the voltage source from OUT and apply 1.002V to IN, what voltage do you expect to see out OUT?

3 - (0.0	102/(100) = 2.81	/ (3-	(0.002)(10,000)	= -17V
age on IN	voltage on OUT	current into IN	current into OLIT	

		CANAL CONTRACTOR CONTR			
voltage on IN	voltage on OUT	current into IN	current into OUT		
1V	3V	0	0		
1.001V	3V	. 0	10uA		
1V	3.001V	0	1nA		
	1V	1V 3V 1.001V 3V	1V 3V 0 1.001V 3V 0		

6) [10] You have made a bandgap reference similar to the one in Lab 5. *Carefully* sketch the voltage across the diode, the voltage across resistor R₁, and the voltage at the drain of M1, all vs. temperature for T=-40 to +85C. "Carefully" means label each axis and draw clearly. Assume that the diode voltage is 0.6V at 25C, and ln(N)=1.

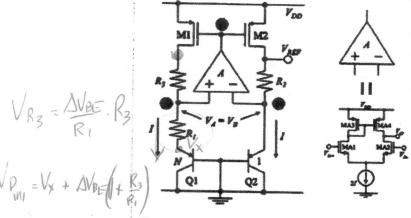
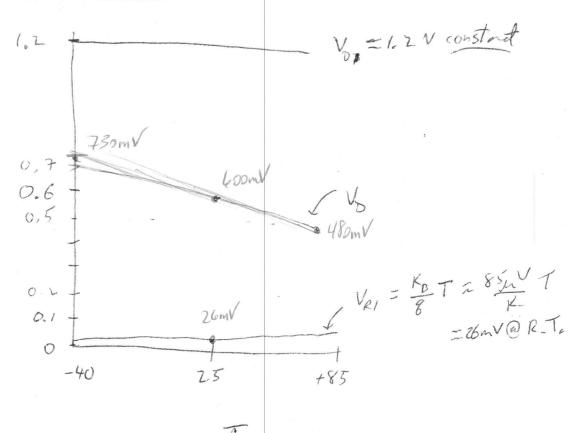
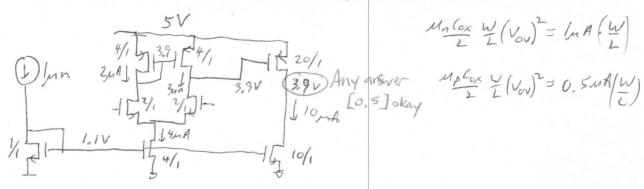


Fig. 6: A CMOS bandgap voltage reference using erroramplifier-based current mirror. Slope of Vo: 3 pts (VR.) Slope of DVRES 3 pts stope May 4 MID: 4 pts



- 7) [16] Design an NMOS-input two-stage op-amp with the following specs:
 - 2uA flowing in each input device and 10uA flowing in the output devices
 - 100mV overdrive voltages
 - 1um channel lengths
 - V_{DD} =5V. $\mu_n C_{ox}$ =200uA/V², $\mu_p C_{ox}$ =100uA/V², $|V_{tp}|$ = V_{tn} =1V, λ =1/(10V) You may use a single 1uA ideal current source or sink. Draw a clean, clear schematic, label your devices, label node voltages and branch currents.



$$G_{mi} = \frac{2T_0}{V_{osd}} = \frac{4mA}{100mV} = 40_{mS}$$

$$G_{mi} = \frac{20_{mA}}{100mV} = 200_{mS}$$

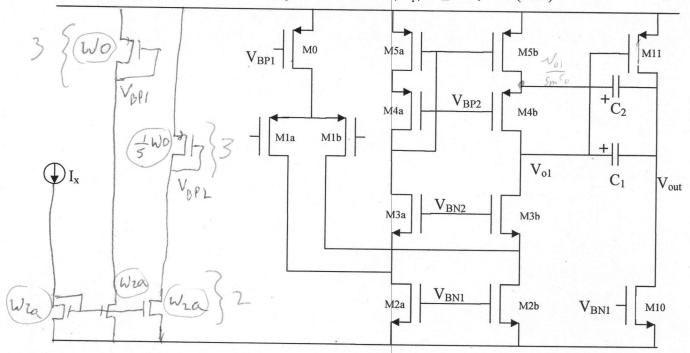
$$R_{01} = \frac{1}{2} \frac{10V}{2mA} = 2.5m\Omega$$

$$R_{02} = \frac{1}{2} \frac{10V}{10_{mA}} = 500K\Omega$$

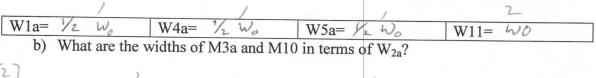
$$R_{02} = \frac{1}{2} \frac{10V}{10_{mA}} = 500K\Omega$$

- 8) [8] For the previous problem,
 - a) what is the input common mode range [1.2] 4.9]
 - b) output swing [0.1, 4.9]
 - c) low frequency gain 10,000
 - d) output pole with a 10fF load capacitor?

- 9) [20] For the amplifier below, assume that you have designed the circuit such that
 - $I_{D0} = I_{D2a} = I_{D10}$
 - 100mV overdrive voltages, 1um channel lengths
 - $V_{OUT} = V_{DD}/2$
 - V_{DD} =5V. $\mu_n C_{ox}$ =200uA/V², $\mu_p C_{ox}$ =100uA/V², $|V_{tp}|$ = V_{tn} =1V, λ =1/(10V)

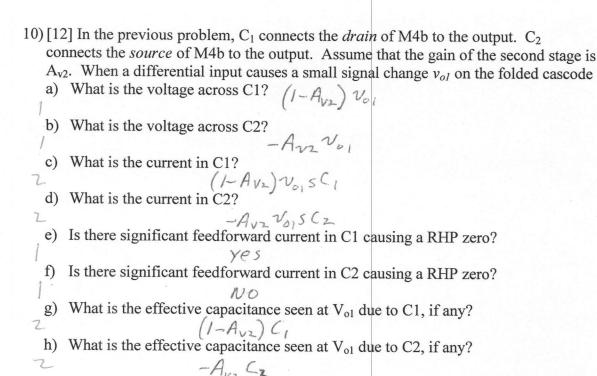


a) What are the widths of M1a, M4a, M5a and M11 in terms of W_0 ?



Ba= $\frac{1}{2}$ $\frac{1}{2}$ $\frac{1}{2}$ $\frac{1}{2}$ W10= $\frac{1}{2}$ $\frac{1}{2}$ What is the bias voltage on V_{ol} with V_{id} =0? 3 9 VW3a=

- d) What is the input common mode range? $\left[\sqrt{800 100} \right] = 0.9 \times 10^{-100}$ [2] e) What is the output swing?
- [2] f) Using the ideal current source with current $I_x=I_{D0}$, design the bias circuitry just for the PMOS gates, V_{BP1} and V_{BP2} . Label device sizes relative to W0 and W2a.



11) [10] Consider a simple two-transistor amplifier: an NMOS-input common source amplifier with PMOS load. Assume that the PMOS device has an overdrive voltage twice the NMOS overdrive voltage.

a) What is the PMOS transconductance, g_{mp} , in terms of the NMOS transconductance g_{mn} ? $g_{mp} = \frac{2 \, \mathcal{I}_{mp}}{\sqrt{g_{mp}}} = \frac{2}{2} \, g_{mp}$

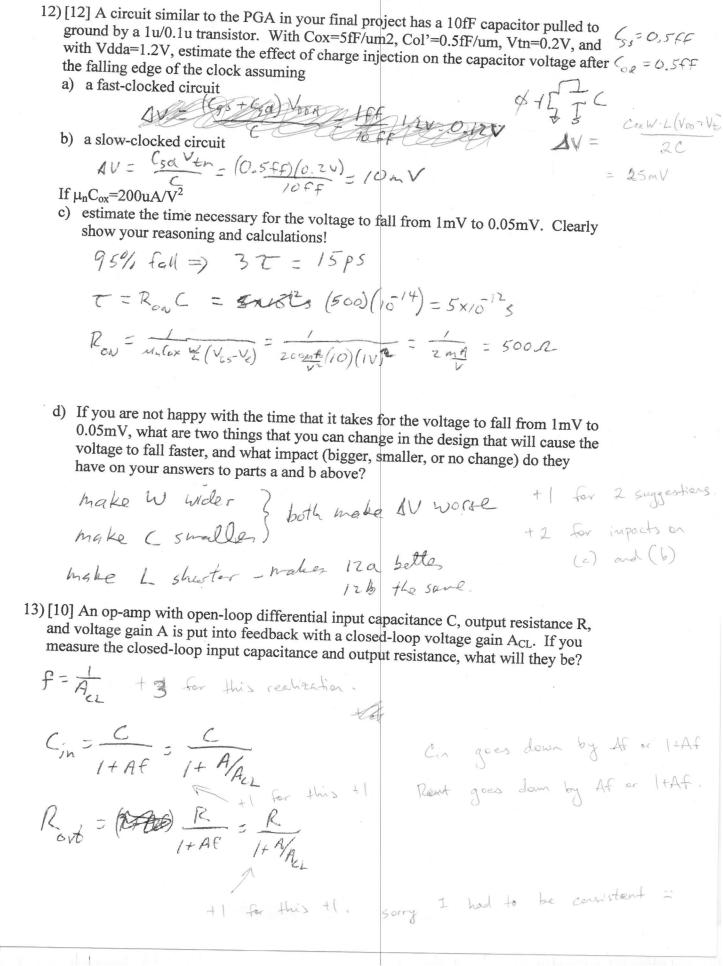
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b) What is the gain from the PMOS device to the output, A_{vp} , in terms of the NMOS gain to the output, A_{vn} ? $A_{vp} = \frac{1}{2} A_{vp}$

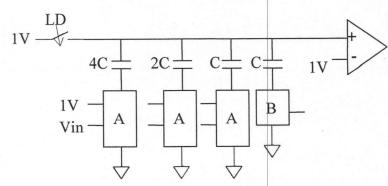
c) What is the thermal noise voltage in the PMOS device, v_{np} , in terms of the thermal noise voltage in the NMOS device, v_{nn} ? $\overline{v_{np}} = 4k_{D}t \frac{1}{g_{nn}} Of = 2 \overline{v_{np}}$ $\overline{v_{np}} = \sqrt{2} v_{np}$

d) What is the total output noise power, $(v_{\text{noise,out}})^2$? $V_{n,n} A_{vn} + V_{n,p} A_{vp} = V_{n,n} A_{vn} (1 + 2(\frac{1}{2})) = \frac{3}{2} V_{n,n} A_{vn} A_{vn}$

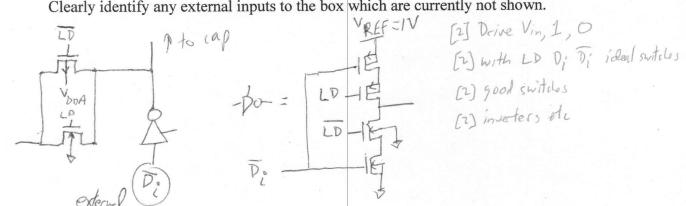
e) What is the total equivalent input noise power, $(v_{noise,inputEQ})^2$ in terms of the NMOS noise voltage?



14) [16] Many student projects used a topology like the following ADC in their final projects. An external digital SAR circuit takes a clock and the comparator output and generates the LD and Di signals.



a) design the circuitry that goes inside of the boxes labeled A, assuming that Vin is loaded on the bottom plates of the capacitors during the LD phase, and then the bottom plate is switched between 1V and ground in subsequent clock cycles. Clearly identify any external inputs to the box which are currently not shown.



b) Assuming the SAR drives the signals to the boxes properly, sketch the waveforms on LD, the digital control bits D2, D1, and D0, and V+ when the input Vin = 0.6V

